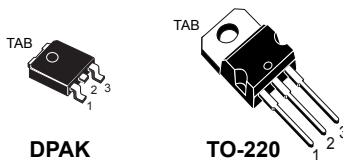
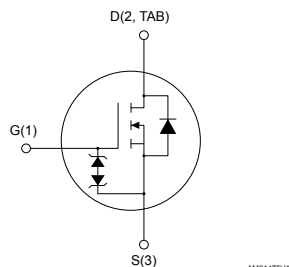


## N-channel 525 V, 0.72 $\Omega$ typ., 6 A, MDmesh™ K3 Power MOSFETs in DPAK and TO-220 packages



DPAK

TO-220



AM01475V1

### Features

Order codes	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$	$P_{TOT}$
STD7N52K3	525 V	0.85 $\Omega$	6 A	90 W
STP7N52K3				

- 100% avalanche tested
- Extremely high dv/dt capability
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

### Applications

- Switching applications

### Description

These MDmesh™ K3 Power MOSFETs are the result of improvements applied to STMicroelectronics' MDmesh™ technology, combined with a new optimized vertical structure. These devices boast an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering them suitable for the most demanding applications.

#### Product status links

[STD7N52K3](#)
[STP7N52K3](#)

#### Product summary

##### STD7N52K3

<b>Order code</b>	STD7N52K3
-------------------	-----------

<b>Marking</b>	7N52K3
----------------	--------

<b>Package</b>	DPAK
----------------	------

<b>Packing</b>	Tape and reel
----------------	---------------

##### STP7N52K3

<b>Order code</b>	STP7N52K3
-------------------	-----------

<b>Marking</b>	7N52K3
----------------	--------

<b>Package</b>	TO-220
----------------	--------

<b>Packing</b>	Tube
----------------	------

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	6	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3.8	A
$I_{DM}^{(1)}$	Drain current (pulsed)	24	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
$I_{AR}^{(2)}$	Avalanche current, repetitive or non-repetitive	3	A
$E_{AS}^{(3)}$	Single pulse avalanche energy	100	mJ
ESD	Gate-source human body model (C = 100 pF, R = 1.5 k $\Omega$ )	2.5	kV
dv/dt <sup>(4)</sup>	Peak diode recovery voltage slope	12	V/ns
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2. Pulse width is limited by  $T_{Jmax}$ .
3. Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{ V}$
4.  $I_{SD} \leq 6\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

**Table 2. Thermal data**

Symbol	Parameter	Value		Unit
		DPAK	TO-220	
$R_{thj-case}$	Thermal resistance junction-case	1.39		$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50		$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient		62.5	$^\circ\text{C}/\text{W}$

1. When mounted on an 1-inch<sup>2</sup> FR-4, 2oz Cu board.

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	525			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 525\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 525\text{ V}$ , $T_C = 125\text{ °C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$		0.72	0.85	$\Omega$

1. Defined by design, not subject to production test.

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 50\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	870	-	$\text{pF}$
$C_{oss}$	Output capacitance			70		
$C_{rss}$	Reverse transfer capacitance			13		
$C_{oss(tr)}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }420\text{ V}$ , $V_{GS} = 0\text{ V}$ ,	-	53	-	$\text{pF}$
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	3.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 420\text{ V}$ , $I_D = 6\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 17. Test circuit for gate charge behavior)	-	33	-	$\text{nC}$
$Q_{gs}$	Gate-source charge			6		
$Q_{gd}$	Gate-drain charge			21		

1.  $C_{oss(tr)}$  is defined as the constant equivalent capacitance giving the same storage energy as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 420 V.

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 260\text{ V}$ , $I_D = 3\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 16. Test circuit for resistive load switching times and Figure 21. Switching time waveform)	-	13	-	$\text{ns}$
$t_r$	Rise time			11		
$t_{d(off)}$	Turn-off delay time			36		
$t_f$	Fall time			19		

**Table 6. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$I_{SD}$	Source-drain current		-		6	A	
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				24		
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 6\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V	
$t_{rr}$	Reverse recovery time	$I_{SD} = 6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see Figure 18. Test circuit for inductive load switching and diode recovery times)	-	220		ns	
$Q_{rr}$	Reverse recovery charge			1.8			μC
$I_{RRM}$	Reverse recovery current			16			
$t_{rr}$	Reverse recovery time	$I_{SD} = 6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ °C}$ (see Figure 18. Test circuit for inductive load switching and diode recovery times)	-	250		ns	
$Q_{rr}$	Reverse recovery charge			2.2			μC
$I_{RRM}$	Reverse recovery current			18			

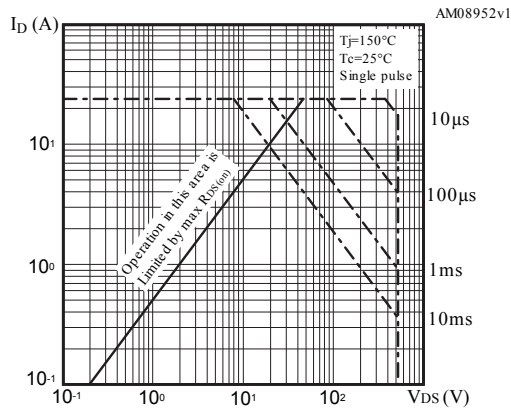
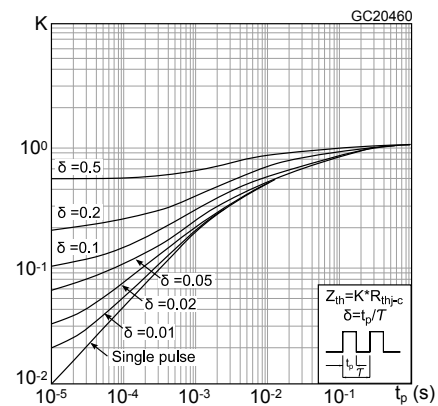
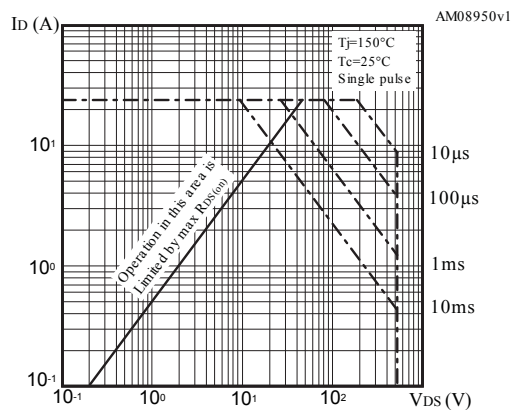
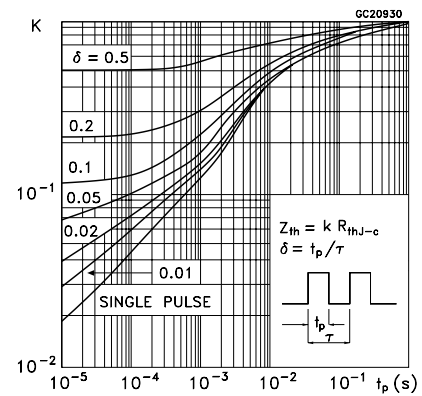
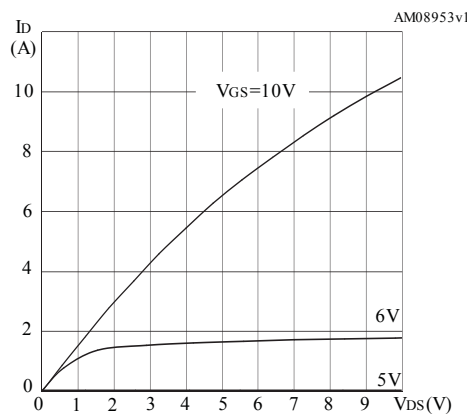
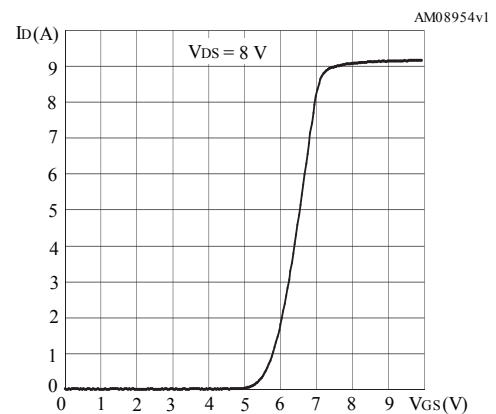
1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs, duty cycle 1.5%.

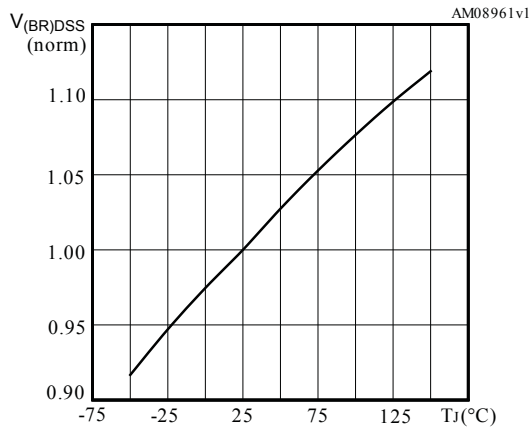
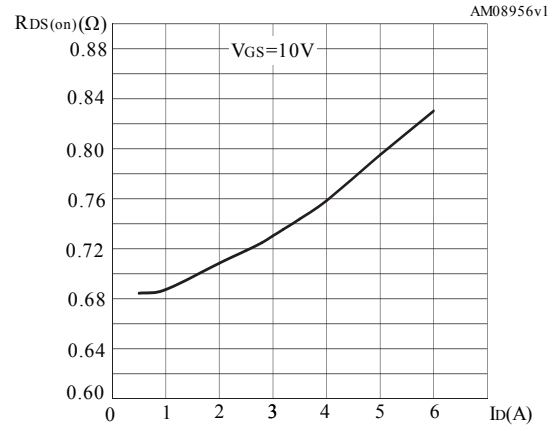
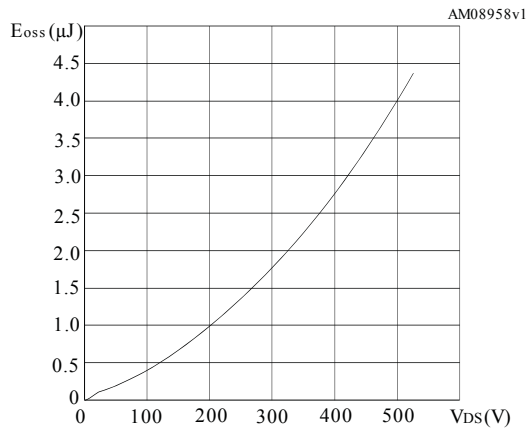
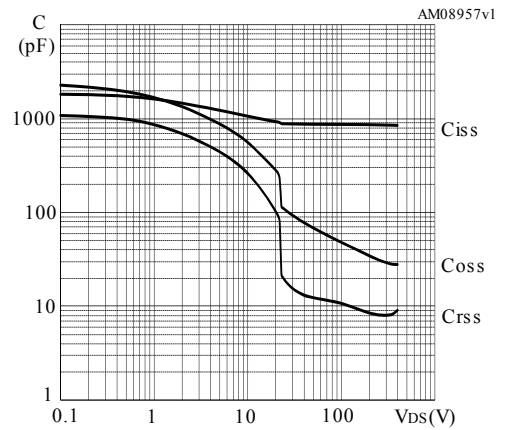
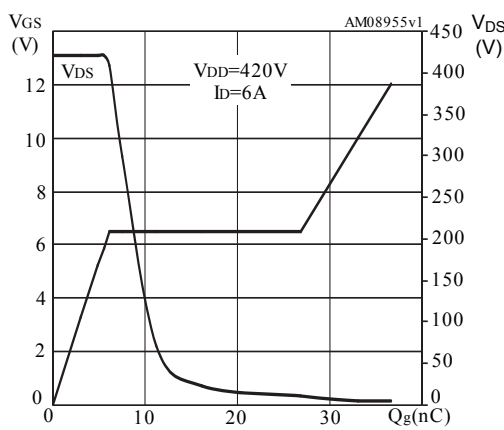
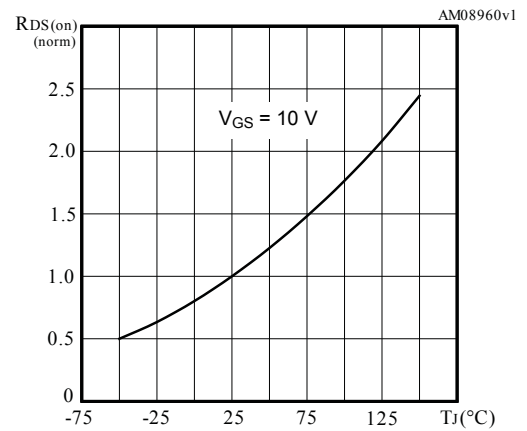
**Table 7. Gate-source Zener diode**

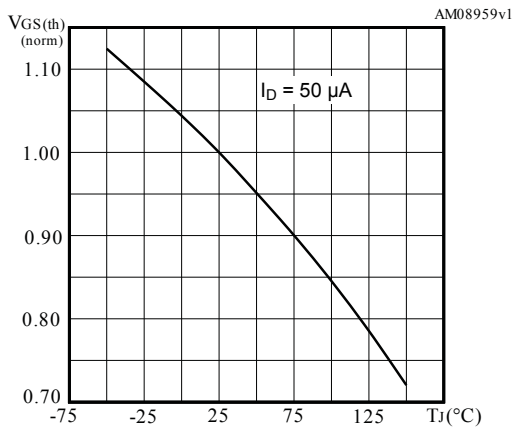
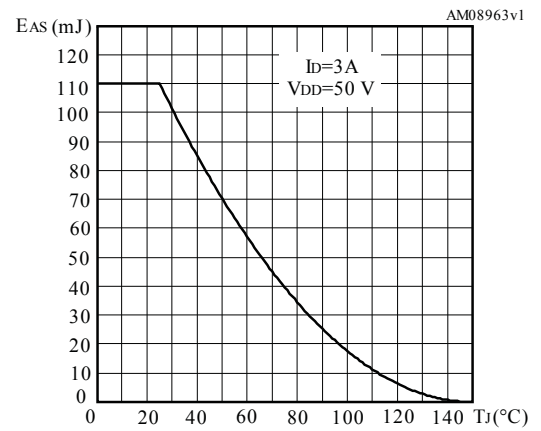
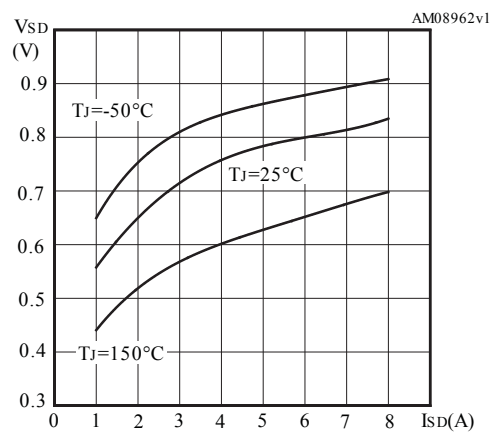
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)

**Figure 1. Safe operating area for DPAK**

**Figure 2. Thermal impedance for DPAK**

**Figure 3. Safe operating area for TO-220**

**Figure 4. Thermal impedance for TO-220**

**Figure 5. Output characteristics**

**Figure 6. Transfer characteristics**


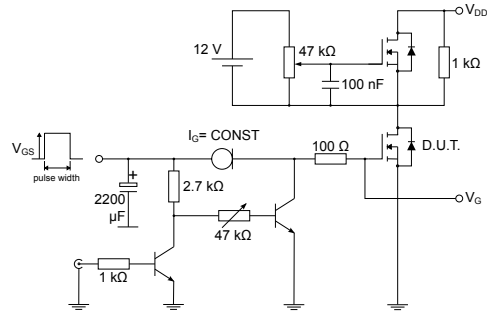
**Figure 7. Normalized  $V_{(BR)DSS}$  vs temperature**

**Figure 8. Static drain-source on-resistance**

**Figure 9. Output capacitance stored energy**

**Figure 10. Capacitance variations**

**Figure 11. Gate charge vs gate-source voltage**

**Figure 12. Normalized on-resistance vs temperature**


**Figure 13. Normalized gate threshold voltage vs temperature**

**Figure 14. Maximum avalanche energy vs temperature**

**Figure 15. Source-drain diode forward characteristics**


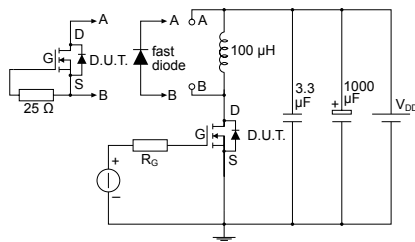
### 3 Test circuits

**Figure 16. Test circuit for resistive load switching times**

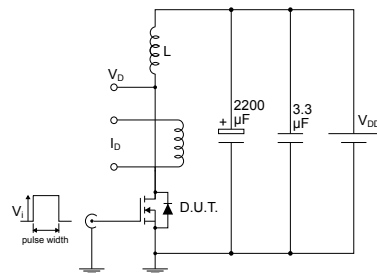

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**Figure 17. Test circuit for gate charge behavior**


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**Figure 18. Test circuit for inductive load switching and diode recovery times**


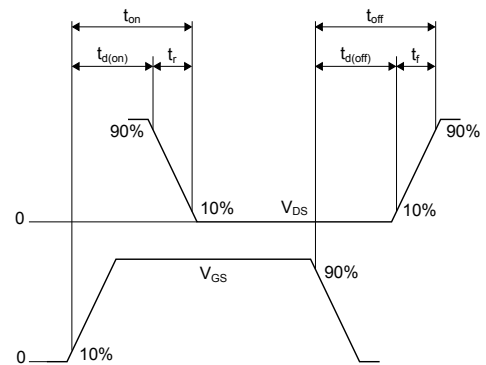
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**Figure 19. Unclamped inductive load test circuit**


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**Figure 20. Unclamped inductive waveform**


AM01472v1

**Figure 21. Switching time waveform**


AM01473v1



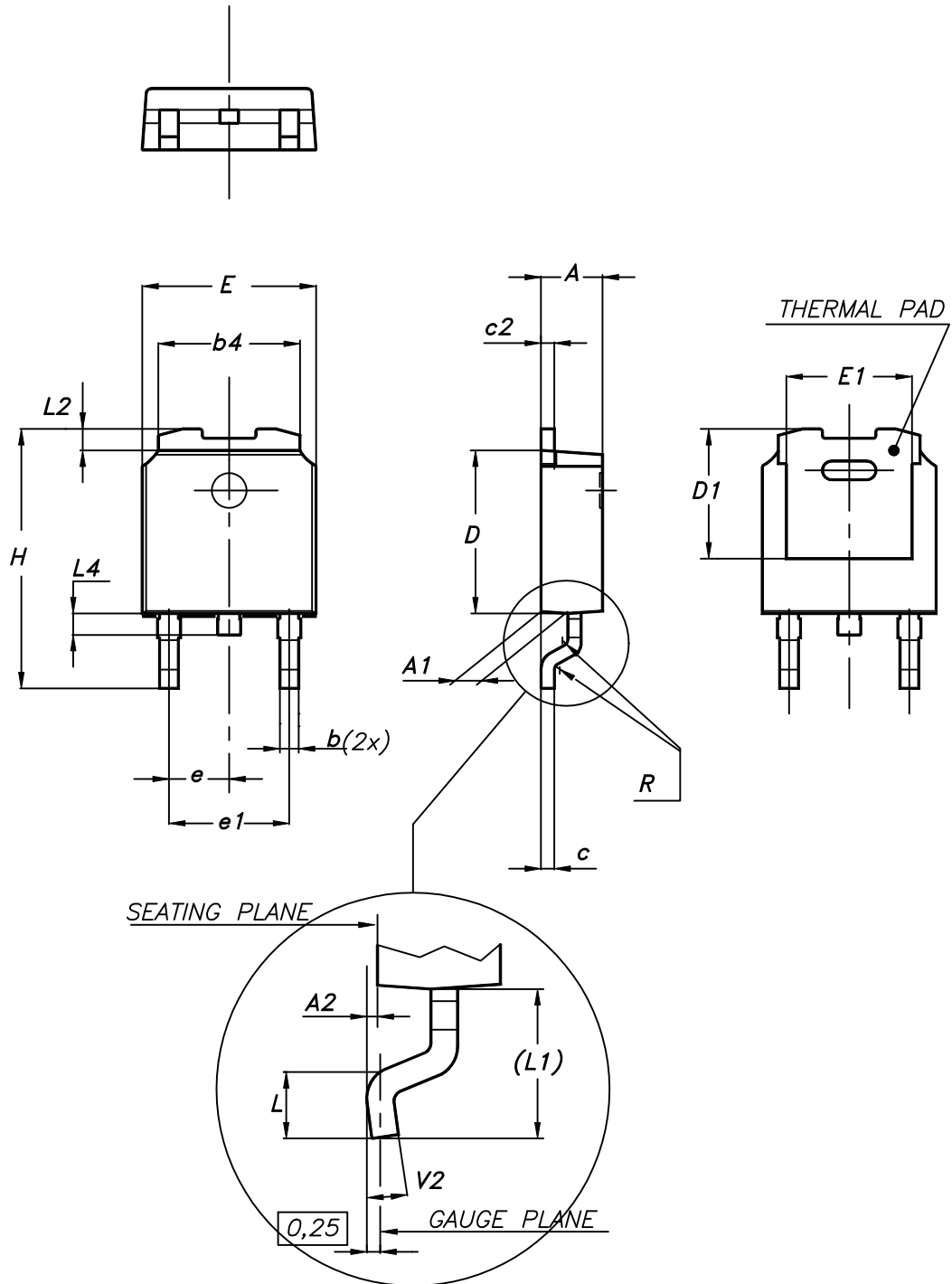
## 4 Package information

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In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 DPAK (TO-252) type A2 package information

Figure 22. DPAK (TO-252) type A2 package outline



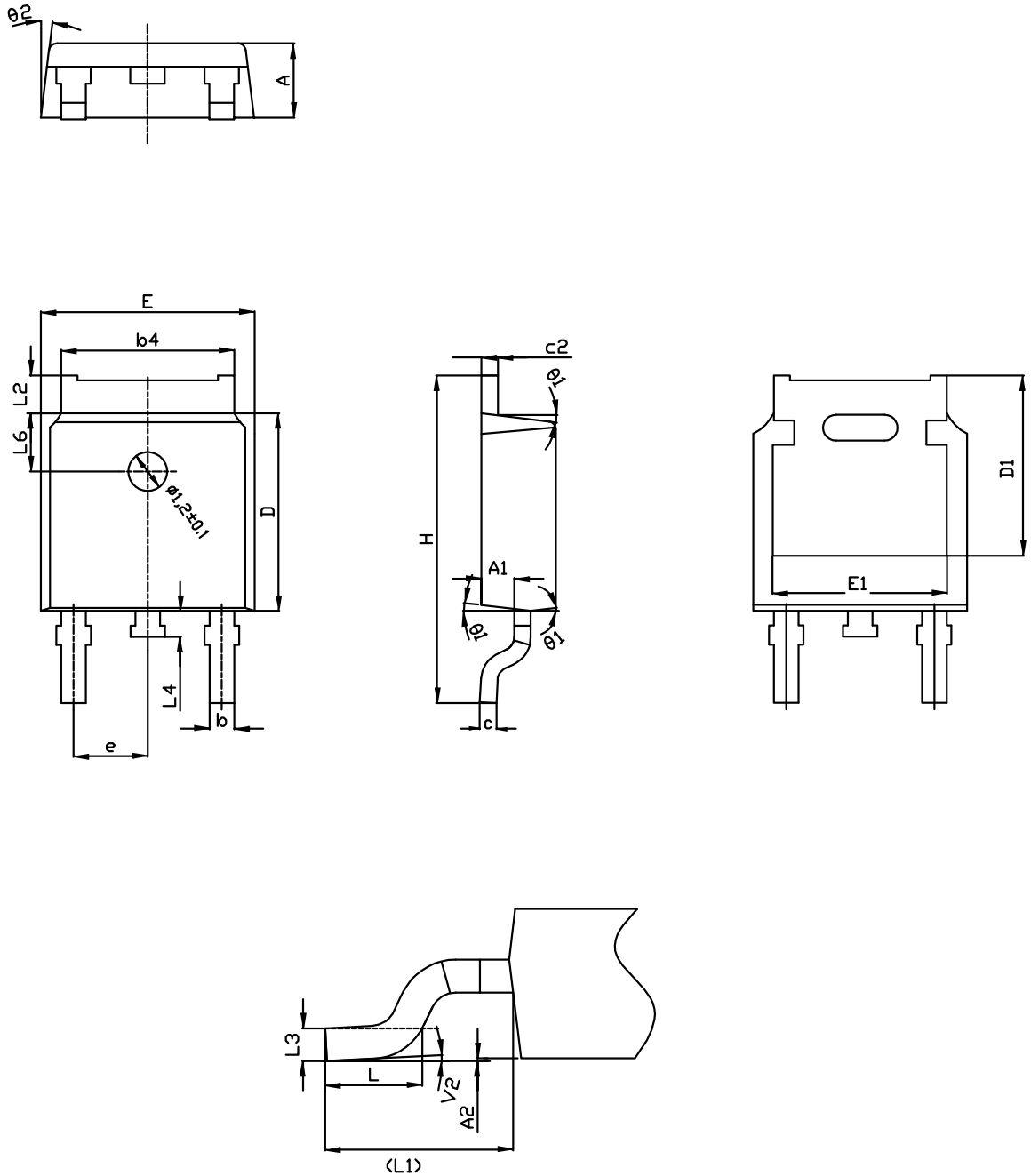
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**Table 8. DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

## 4.2 DPAK (TO-252) type C2 package information

Figure 23. DPAK (TO-252) type C2 package outline

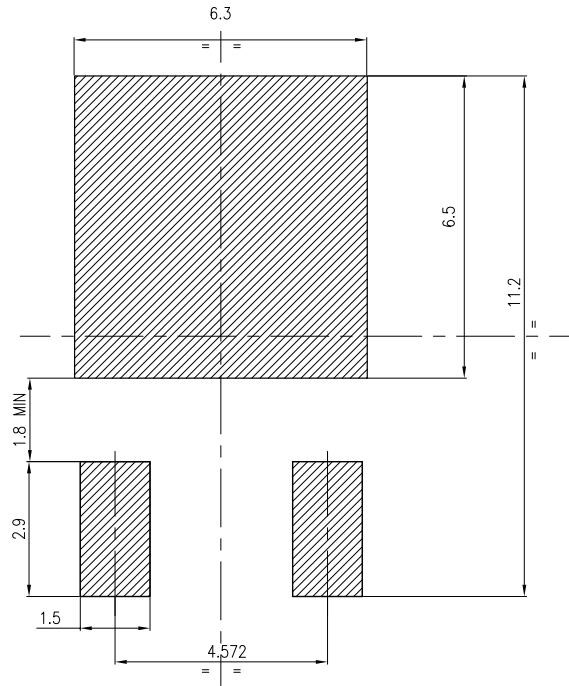


0068772\_C2\_25

**Table 9. DPAK (TO-252) type C2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.10		5.60
E	6.50	6.60	6.70
E1	5.20		5.50
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

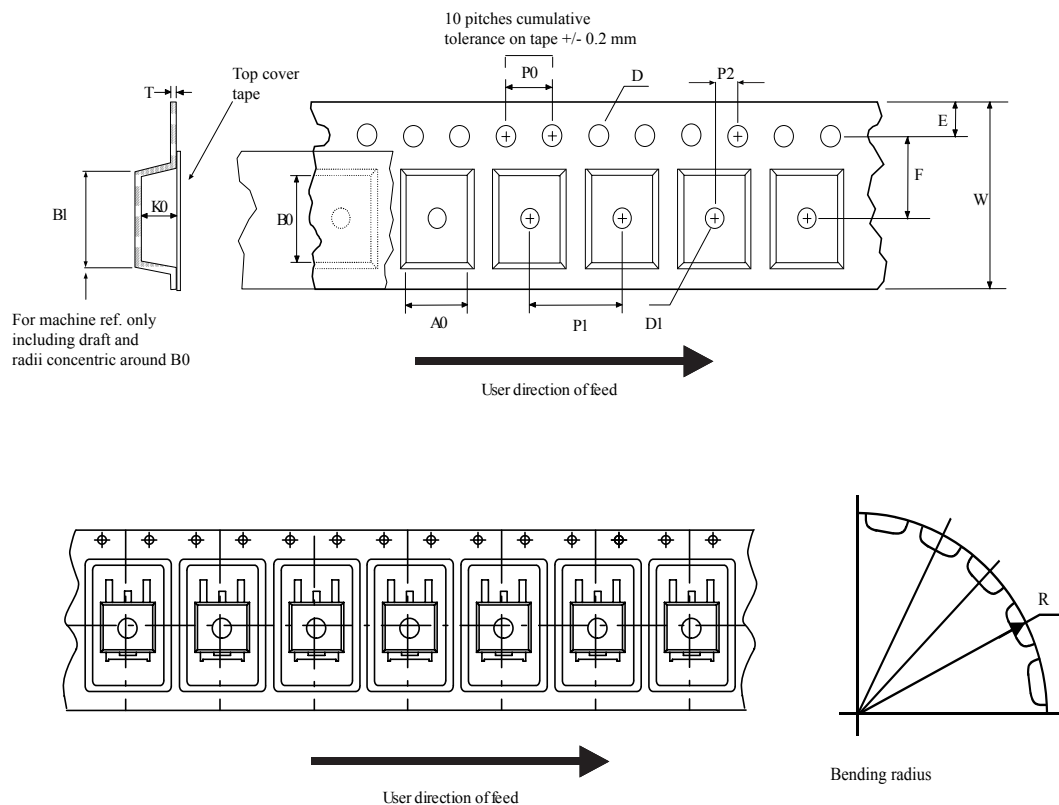
**Figure 24. DPAK (TO-252) recommended footprint (dimensions are in mm)**



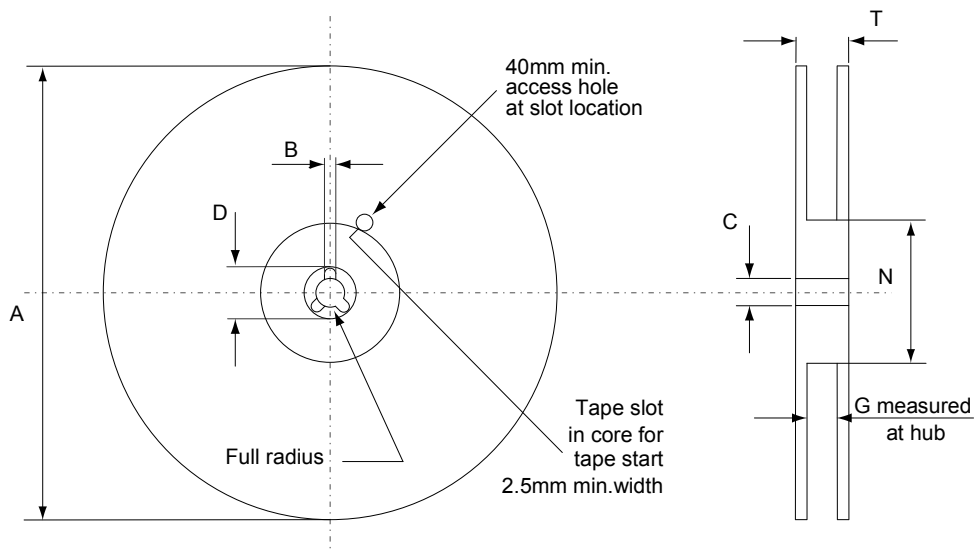
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### 4.3 DPAK (TO-252) packing information

Figure 25. DPAK (TO-252) tape outline



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**Figure 26. DPAK (TO-252) reel outline**


AM06038v1

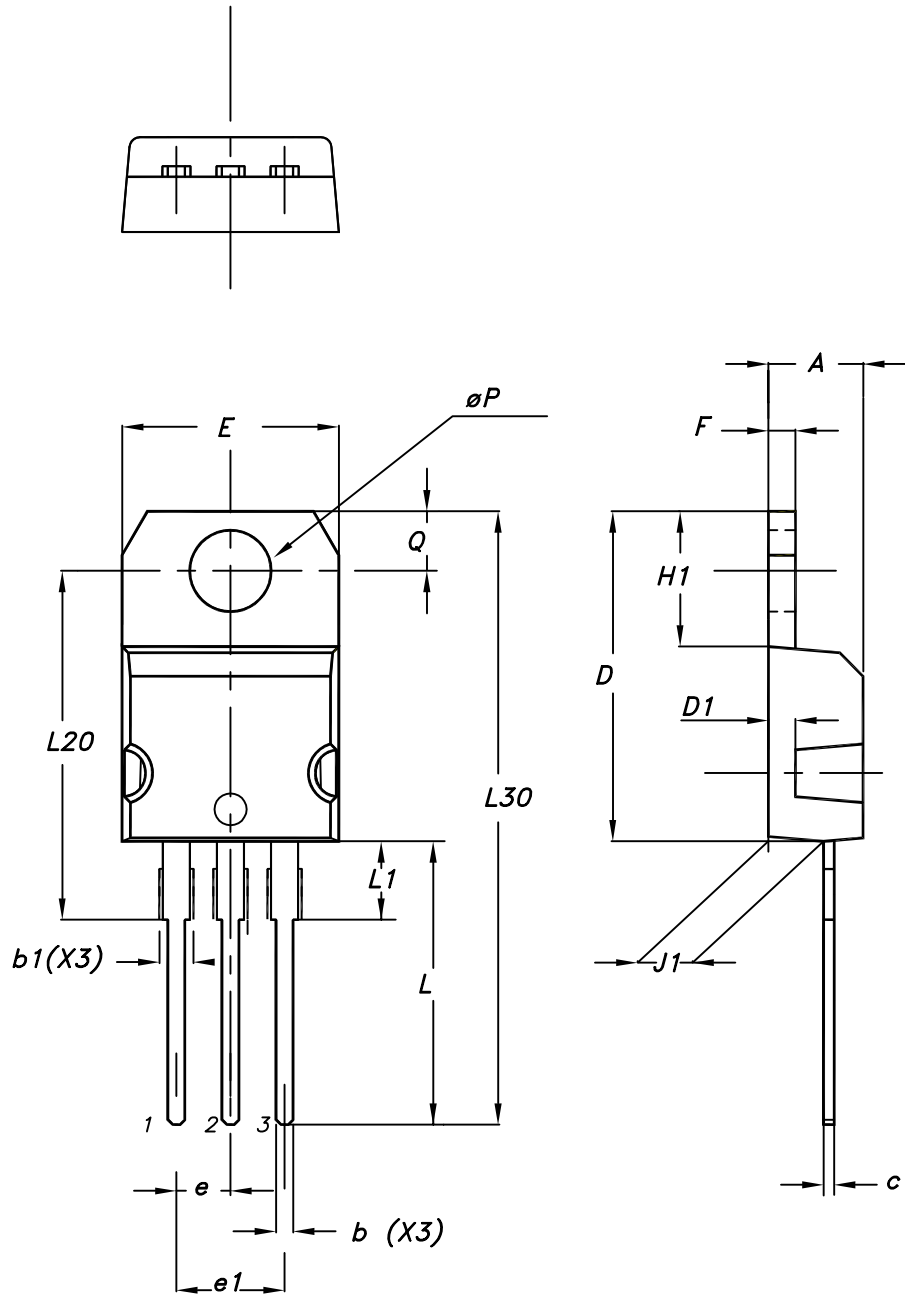
**Table 10. DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			



#### 4.4 TO-220 type A package information

Figure 27. TO-220 type A package outline



0015988\_typeA\_Rev\_21

**Table 11. TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

## Revision history

**Table 12. Document revision history**

Date	Version	Changes
07-Jul-2008	1	First release.
10-Sep-2009	2	Document status promoted from preliminary data to datasheet.
27-Jun-2011	3	<i>Section 2.1: Electrical characteristics (curves)</i> has been updated.
07-Mar-2012	4	Updated <i>Section 4: Package mechanical data</i> . Minor text changes.
11-Jul-2018	5	Part numbers STB7N52K3 and STF7N52K3 have been moved to a different datasheet, and the document has been updated accordingly. Updated features and description on cover page. Updated <i>Table 1. Absolute maximum ratings</i> . Updated <i>Section 4.1 DPAK (TO-252) type A2 package information</i> . Minor text changes.
01-Aug-2018	6	Updated <a href="#">Table 1. Absolute maximum ratings</a> .

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